National Semiconductor

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MM54HCT251/MM74HCT251
8-Channel TRI-STATE® Multiplexer

General Description

This 8-channel digital multiplexer with TRI-STATE outputs utilizes advanced silicon-gate CMOS technology. Along with the high noise immunity and low power consumption of standard CMOS integrated circuits, it possesses the ability to drive 10 LS-TTL loads. The large output drive capability and TRI-STATE feature make this part ideally suited for interfacing with bus lines in a bus oriented system.

This multiplexer features both true (Y) and complement (W) outputs as well as a STROBE input. The STROBE must be at a low logic level to enable this device. When the STROBE input is high, both outputs are in the high impedance state. When enabled, address information on the data select inputs determines which data input is routed to the Y and W outputs.

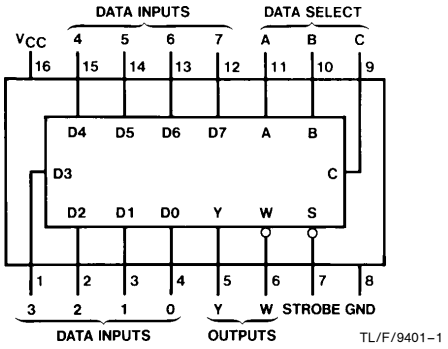
MM54HCT/MM74HCT devices are intended to interface between TTL and NMOS components and standard CMOS devices. These parts are also plug-in replacements for LS-TTL devices and can be used to reduce power consumption in existing designs.

Features

- Typical propagation delay: 20 ns
- Low quiescent current: 40 μA maximum (74HCT Series)
- Low input current: 1 μA maximum
- Fanout of 10 LS-TTL loads
- TTL input compatible

Connection and Logic Diagrams

Dual-in-Line Package



TL/F/9401–1

Top View

Order Number MM54HCT251 or MM74HCT251

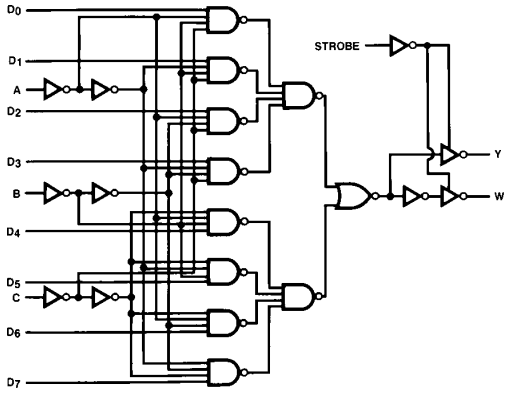
Truth Table

Inputs				Outputs	
Select			Strobe		
C	B	A	S	Y	W
X	X	X	H	Z	Z
L	L	L	L	D0	$\overline{D0}$
L	L	H	L	D1	$\overline{D1}$
L	H	L	L	D2	$\overline{D2}$
L	H	H	L	D3	$\overline{D3}$
H	L	L	L	D4	$\overline{D4}$
H	L	H	L	D5	$\overline{D5}$
H	H	L	L	D6	$\overline{D6}$
H	H	H	L	D7	$\overline{D7}$

H = high logic level, L = logic level

X = irrelevant, Z = high impedance (off)

D0, D1 . . . D7 = the level of the respective D input



TL/F/9401–2

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Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5V to +7.0V
DC Input Voltage (V_{IN})	−1.5V to V_{CC} +1.5V
DC Output Voltage (V_{OUT})	−0.5V to V_{CC} +0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per Pin (I_{OUT})	±35 mA
DC V_{CC} or GND Current, per Pin (I_{CC})	±70 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T_L) (Soldering, 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HCT	−40	+85	°C
MM54HCT	−55	+125	°C
Input Rise or Fall Times (t_r, t_f) V_{CC} = 4.5V		500	ns

DC Electrical Characteristics (Note 4) V_{CC} = 5V ±10%

Symbol	Parameter	Conditions	T_A = 25°C	74HCT T_A = −40°C to +85°C	54HCT T_A = −55°C to +125°C	Units
			Typ	Guaranteed Limits		
V_{IH}	Minimum High Level Input Voltage			2.0	2.0	2.0	V
V_{IL}	Maximum Low Level Input Voltage			0.8	0.8	0.8	V
V_{OH}	Minimum High Level Output Voltage	V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 20\ \mu A$	4.5	4.4	4.4	4.4	V
		V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 4.0$ mA, V_{CC} = 4.5V	4.2	3.98	3.84	3.7	V
		$\|I_{OUT}\| \le 4.8$ mA, V_{CC} = 5.5V	5.2	4.98	4.84	4.7	V
V_{OL}	Maximum Low Level Output Voltage	V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 20\ \mu A$	0	0.1	0.1	0.1	V
		V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 4.0$ mA, V_{CC} = 4.5V	0.2	0.26	0.33	0.4	V
		$\|I_{OUT}\| \le 4.8$ mA, V_{CC} = 5.5V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	V_{IN} = V_{CC} or GND		±0.1	±1.0	±1.0	μA
I_{OZ}	Maximum TRI-STATE Output Leakage	V_{OUT} = V_{CC} or GND STROBE = V_{CC}		±0.5	±5.0	±10	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND I_{OUT} = 0 μA		8.0	80	160	μA
		V_{IN} = 2.4V or 0.5V	0.25	0.4	0.55	0.65	mA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C; ceramic "J" package: −12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

AC Electrical Characteristics $V_{CC}=5V$, $T_A=25°C$, $C_L=15$ pF, $t_r=t_f=6$ ns

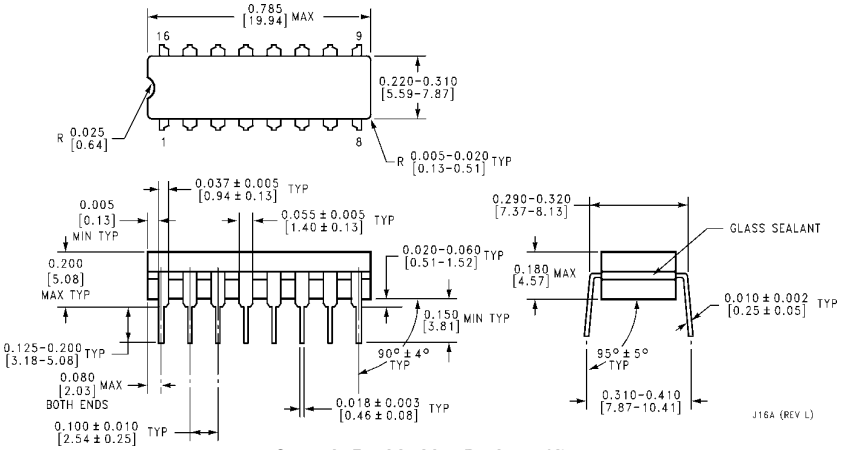
Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay A, B or C to Y		26	35	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, A, B or C to W		27	35	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Any D to Y		22	31	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Any D to W		24	32	ns
t_{PZH}, t_{PZL}	Maximum Output Enable Time, W Output	$R_L=1\ k\Omega$ $C_L=50$ pF	19	27	ns
t_{PZH}, t_{PZL}	Maximum Output Enable Time, Y Output	$R_L=1\ k\Omega$ $C_L=50$ pF	19	26	ns
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time W Output	$R_L=1\ k\Omega$ $C_L=5$ pF	26	40	ns
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time Y Output	$R_L=1\ k\Omega$ $C_L=5$ pF	27	40	ns

AC Electrical Characteristics $V_{CC}=5.0V\pm10\%$, $C_L=50$ pF, $t_r=t_f=6$ ns (unless otherwise specified)

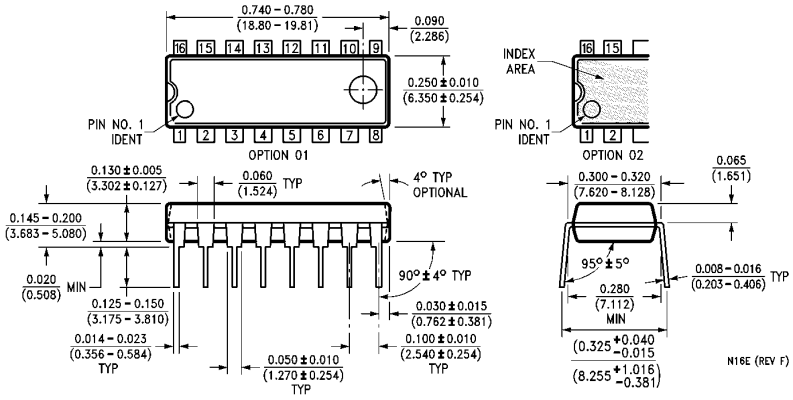
Symbol	Parameter	Conditions	$T_A=25°C$	74HC $T_A=-40°C$ to $+85°C$		54HC $T_A=-55°C$ to $+125°C$	Units
			Typ	Guaranteed Limits			
t_{PHL}, t_{PLH}	Maximum Propagation Delay A, B or C to Y		33	46	58	69	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, A, B or C to W		33	46	58	69	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, any D to Y		27	40	50	60	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, any D to W		27	40	50	60	ns
t_{PZH}, t_{PZL}	Maximum Output Enable Time W Output	$R_L=1\ k\Omega$	21	30	38	45	ns
t_{PZH}, t_{PZL}	Maximum Output Enable Time Y Output	$R_L=1\ k\Omega$	21	30	38	45	ns
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time W Output	$R_L=1\ k\Omega$	22	40	50	60	ns
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time Y Output	$R_L=1\ k\Omega$	23	40	50	60	ns
t_{THL}, t_{TLH}	Maximum Output Rise and Fall Time		8	15	19	23	ns
C_{PD}	Power Dissipation Capacitance (Note 5)	(per Package)	110				pF
C_{IN}	Maximum Input Capacitance		5	10			pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D=C_{PD}\ V_{CC}^2\ f+I_{CC}\ V_{CC}$, and the no load dynamic current consumption, $I_S=C_{PD}\ V_{CC}\ f+I_{CC}$.

Physical Dimensions inches (millimeters)



Ceramic Dual-In-Line Package (J)
Order Number MM54HCT521J or MM74HCT521J
NS Package Number J16A



Molded Dual-In-Line Package (N)
Order Number MM74HCT251N
NS Package Number N16E

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